

# ABSTRACT

In a cleaning step of a substrate-processing device,  
vacuum drawing is made for the space between an inner  
5 chamber and an outer chamber that receives the inner chamber.  
Temperature of the inner chamber is set higher than the  
temperature of the inner chamber during substrate processing  
and set lower than the temperature of a substrate support  
member. After that, a cleaning gas containing  
10 hexafluoroacetylaceton (Hhfac) is supplied in the inner  
chamber, and substances to be cleaned off adhering inside  
the inner chamber are removed.